JST80N30T2C

30V N-Channel Mosfet

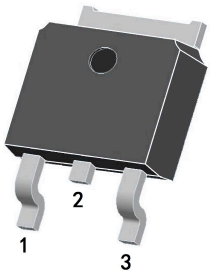
FEATURES

- RDS(ON) < 6mΩ @ VGS = 10V
- RDS(ON) < 12mΩ @ VGS = 4.5V

APPLICATIONS

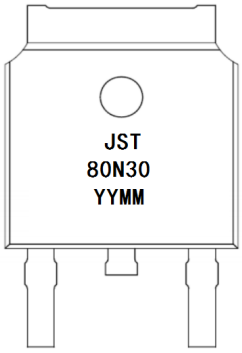
- Load Switch
- PWM Application
- Power management

TO-252



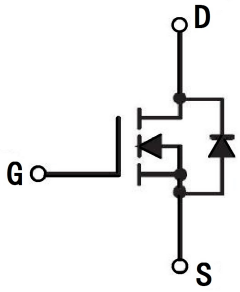
1: G
2: D
3: S

MARKING



YYMM:Date Code(year&month)

N-CHANNEL MOSFET



Absolute Maximum Ratings (T_C=25℃ unless otherwise specified)

Symbol	Parameter		Max.	Units
V_{DSS}	Drain-Source Voltage		30	V
V_{GSS}	Gate-Source Voltage		±20	V
I_D	Continuous Drain Current	T_C = 25℃	70	A
		T_C = 100℃	46	A
I_{DM}	Pulsed Drain Current note1		280	A
E_{AS}	Single Pulsed Avalanche Energy note2		56	mJ
P_D	Power Dissipation	T_C = 25℃	46	W
$R_{\theta JC}$	Thermal Resistance, Junction to Case		2.72	℃/W
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	℃

Electrical Characteristics (T_J=25℃ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V,I_D=250μA	30	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} =30V, V_{GS} = 0V,	-	-	1.0	μA
I_{GSS}	Gate to Body Leakage Current	V_{DS} =0V,V_{GS} = ±20V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}= V_{GS}, I_D=250μA	1.0	1.5	2.5	V
$R_{DS(on)}$	Static Drain-Source on-Resistance note3	V_{GS} =10V, I_D =30A	-	4.8	6	mΩ
		V_{GS} =4.5V, I_D =20A	-	7.5	12	
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} =15V, V_{GS} =0V, f = 1.0MHz	-	1614	-	pF
C_{oss}	Output Capacitance		-	245	-	pF
C_{rss}	Reverse Transfer Capacitance		-	215	-	pF
Q_g	Total Gate Charge	V_{DS} =15V, I_D =30A, V_{GS} =10V	-	33.7	-	nC
Q_{gs}	Gate-Source Charge		-	8.5	-	nC
Q_{gd}	Gate-Drain(“Miller”) Charge		-	7.5	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	V_{DS}=15V, I_D=30A, R_{GEN}=3Ω, V_{GS} =10V	-	7.5	-	ns
t_r	Turn-on Rise Time		-	14.5	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	35.2	-	ns
t_f	Turn-off Fall Time		-	9.6	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	70	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	280	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS} = 0V, I_S=30A	-	-	1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition T_J=25℃,VDD=15V,VG=10V, RG=25Ω, L=0.5mH, IAS=15A

3. Puls Test: Pulse Width≤300μs, Duty Cycle≤0.5%

Typical Performance Characteristics

Figure1: Output Characteristics

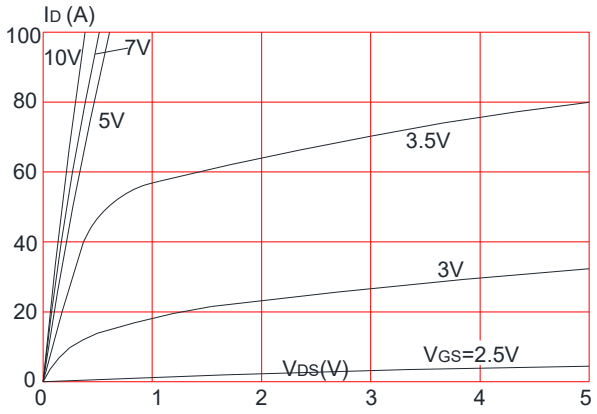


Figure 2: Typical Transfer Characteristics

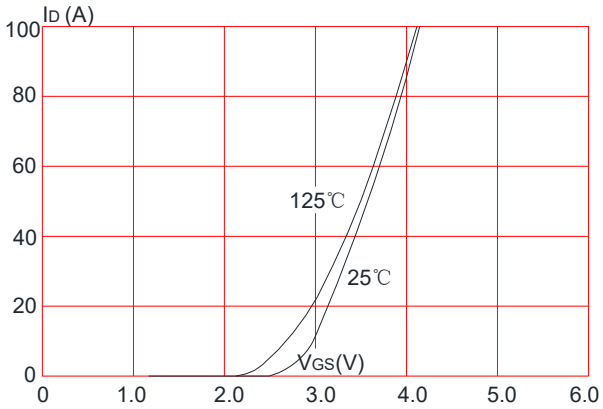


Figure 3: On-resistance vs. Drain Current

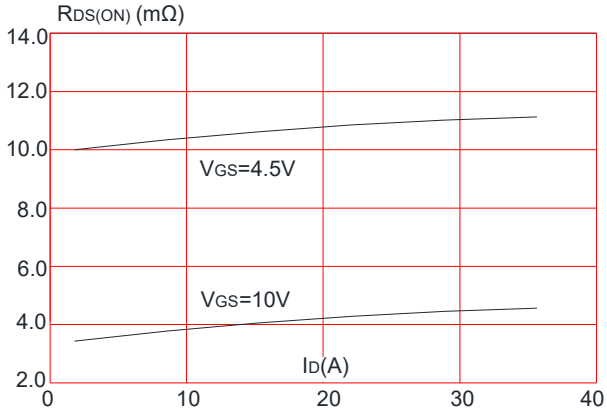


Figure 4: Body Diode Characteristics

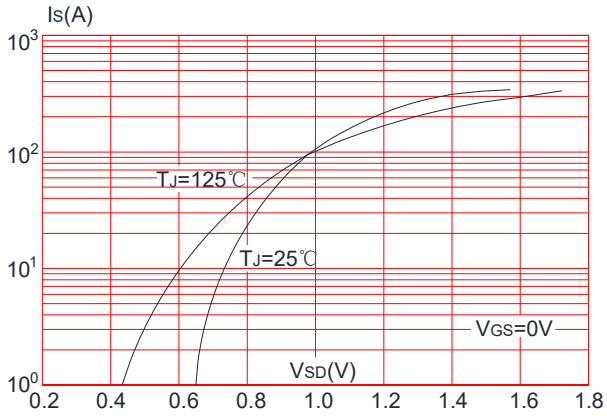


Figure 5: Gate Charge Characteristics

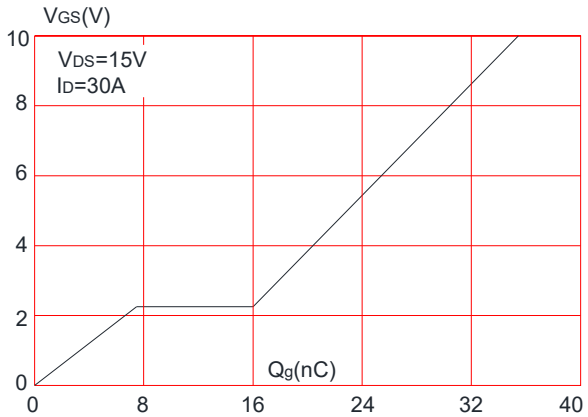


Figure 6: Capacitance Characteristics

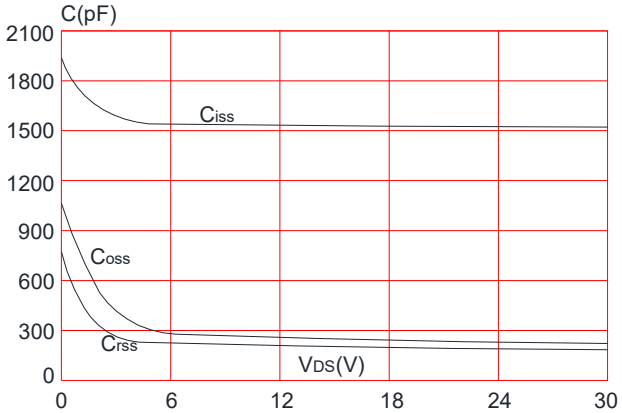


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

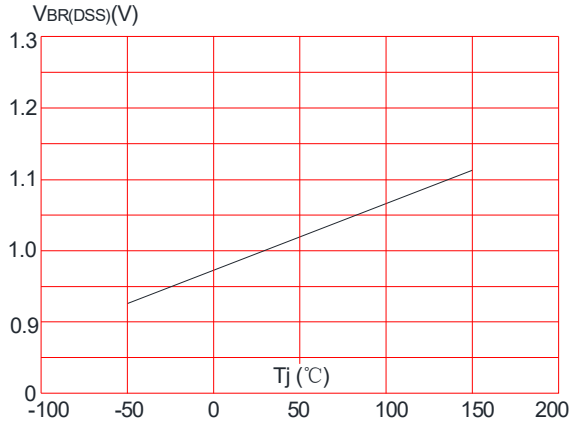


Figure 8: Normalized on Resistance vs. Junction Temperature

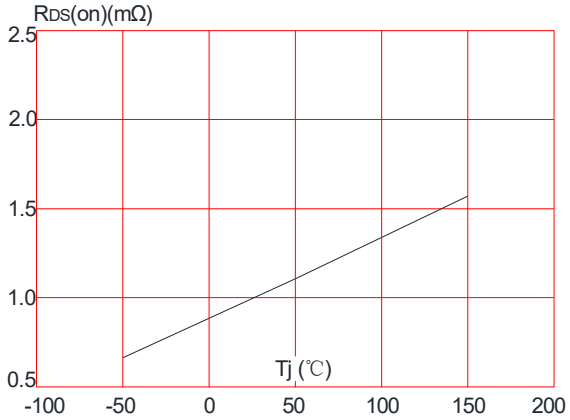


Figure 9: Maximum Safe Operating Area

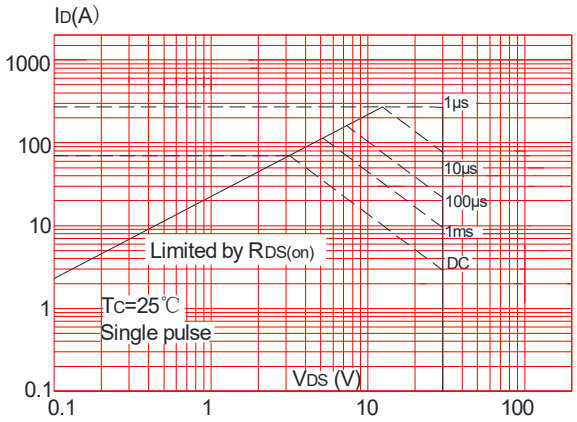


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

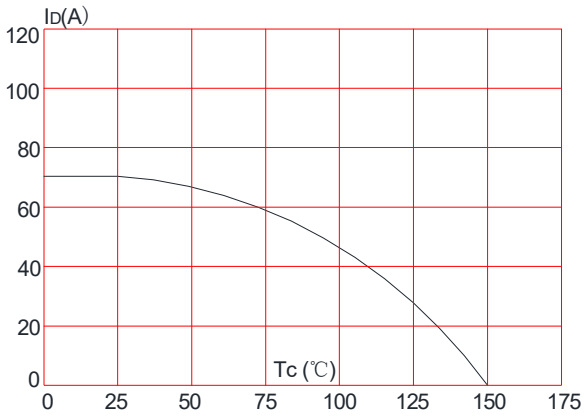
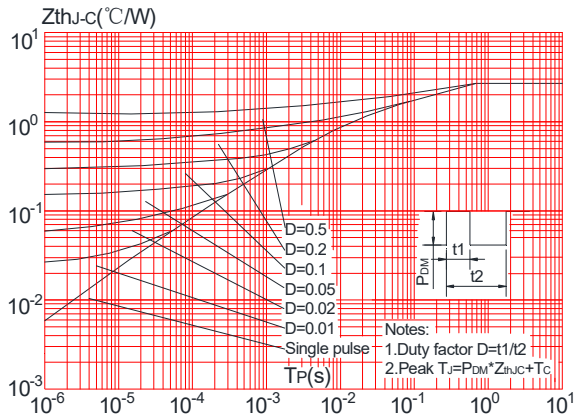
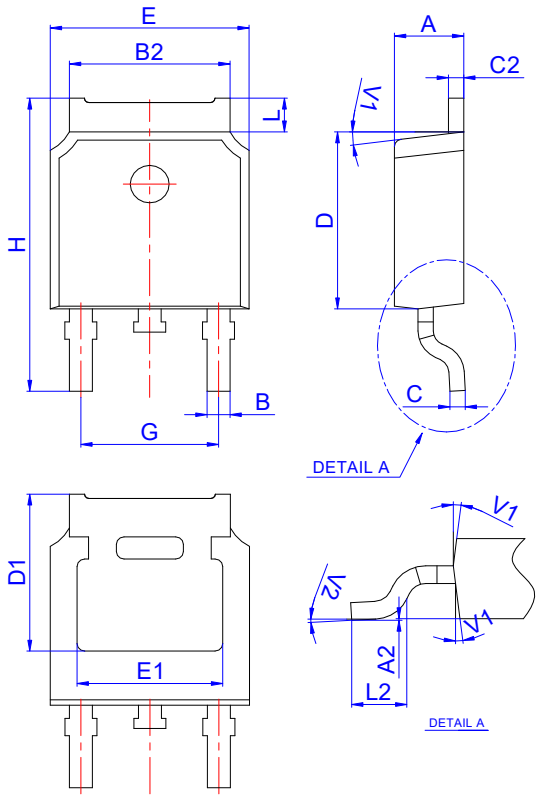


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case



TO-252 PACKAGE OUTLINE DRAWING



Symbols	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°